



**PD IEC TS 62607-12-3:2026**

## BSI Standards Publication

### Nanomanufacturing — Key control characteristics

Part 12-3: 2D material-related products — Schottky barrier heights of 2D material based field-effect transistors: temperature-dependent current-voltage measurements



# National foreword

This Published Document is the UK implementation of IEC TS 62607-12-3:2026.

The UK participation in its preparation was entrusted to Technical Committee NTI/1, Nanotechnologies.

A list of organizations represented on this committee can be obtained on request to its committee manager.

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## Amendments/corrigenda issued since publication

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